

P-Channel Enhancement Mode Power MOSFET

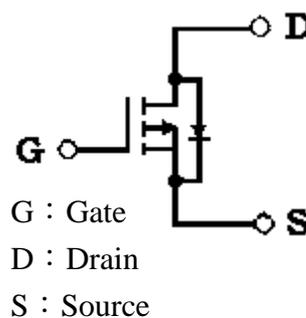
Features:

- Single Drive Requirement
- Low On-resistance
- Fast switching Characteristic
- Pb-free lead plating and halogen-free package

TO-252(DPAK)



B_VD_{SS}	-60V
I_D @ V_{GS}=-10V, T_C=25°C	-42.5A
I_D @ V_{GS}=-10V, T_A=25°C	-8.5A
R_{DS(ON)}@ V_{GS}=-10V, I_D=-17A	15.7mΩ (typ)



Ordering Information

Device	Package	Shipping
KJE15P06	TO-252 (Pb-free lead plating and halogen-free package)	2500 pcs / Tape & Reel

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Drain-Source Voltage	V _{DS}	-60	V	
Gate-Source Voltage	V _{GS}	±20		
Continuous Drain Current @ V _{GS} =-10V, T _C =25°C	I _D	-42.5	A	
Continuous Drain Current @ V _{GS} =-10V, T _C =100°C		-26.9		
Continuous Drain Current @ V _{GS} =-10V, T _A =25°C		-8.5		
Continuous Drain Current @ V _{GS} =-10V, T _A =100°C		-5.4		
Pulsed Drain Current	I _{DM}	-170 *1		
Single Pulse Avalanche Current @ L=0.1mH	I _{AS}	-60		
Single Pulse Avalanche Energy @ L=1mH, I _{AS} =-30A, V _{DD} =-50V	E _{AS}	450 *2	mJ	
Power Dissipation	P _D	T _C =25°C	62.5 *4	W
		T _C =100°C	25 *4	
		T _A =25°C	2.5	
		T _A =100°C	1.0	
Operating Junction and Storage Temperature	T _j , T _{stg}	-55~+150	°C	

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R _{θJC}	2	°C/W
Thermal Resistance, Junction-to-ambient, max	R _{θJA}	50 *3	

Note : *1. Pulse width limited by safe operating area.

*2 . 100% tested by conditions of V_{DD}=-50V, L=0.5mH, V_{GS}=-10V, I_{AS}=-24A.

*3 . The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

*4 . The power dissipation P_D is more useful in setting the upper dissipation limit for cases where additional heatsinking is used. It is used to determined the current rating, when this rating falls below the package limit.

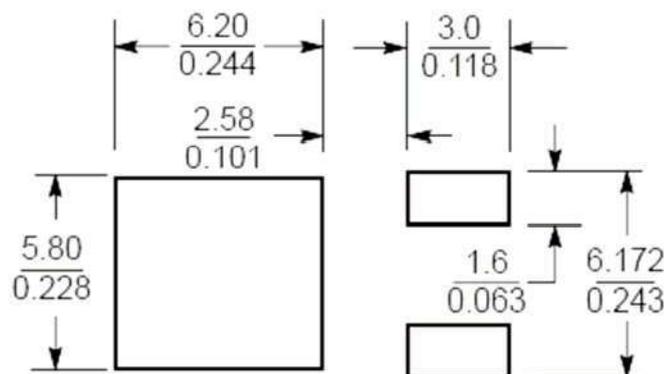
Characteristics (T_j=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	-60	-	-	V	V _{GS} =0V, I _D =-250μA
V _{GS(th)}	-2	-	-4		V _{DS} = V _{GS} , I _D =-250μA
G _{FS}	-	22.9	-	S	V _{DS} =-10V, I _D =-20A
I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
I _{DSS}	-	-	-1	μA	V _{DS} =-60V, V _{GS} =0V
	-	-	-25		V _{DS} =-48V, V _{GS} =0V, T _j =70°C
*R _{DS(ON)}	-	15.7	21	mΩ	V _{GS} =-10V, I _D =-17A
Dynamic					
*Q _g	-	38.4	-	nC	I _D =-17A, V _{DS} =-48V, V _{GS} =-10V
*Q _{gs}	-	8.1	-		
*Q _{gd}	-	12.5	-		

*t _{d(ON)}	-	15.6	-	ns	V _{DS} =-30V, V _{GS} =-10V, R _G =1Ω, I _D =-17A
*t _r	-	25	-		
*t _{d(OFF)}	-	54.2	-		
*t _f	-	19.6	-		
C _{iss}	-	2071	-	pF	V _{GS} =0V, V _{DS} =-30V, f=1MHz
C _{oss}	-	276	-		
C _{rss}	-	117	-		
Source-Drain Diode					
*I _S	-	-	-42.5	A	
*I _{SM}	-	-	-170		
*V _{SD}	-	-0.87	-1.2	V	I _S =-30A, V _{GS} =0V
*t _{rr}	-	15.3	-	ns	I _F =-30A, V _{GS} =0V, dI _F /dt=100A/μs
*Q _{rr}	-	8.7	-	nC	

*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

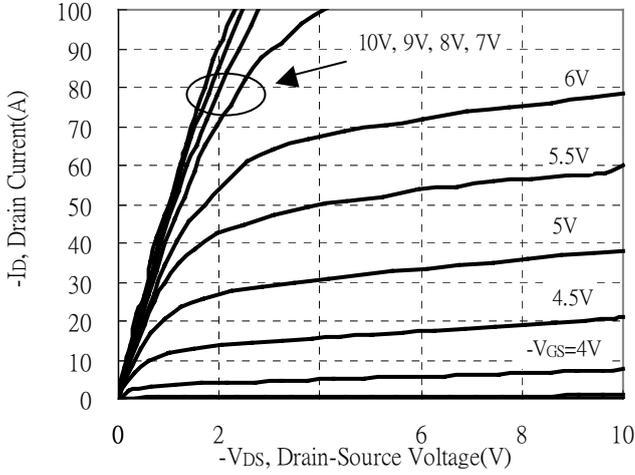
Recommended soldering footprint



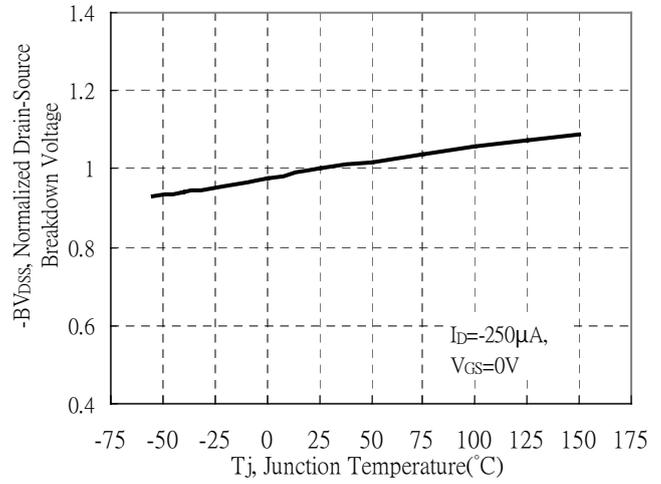
Unit ($\frac{\text{mm}}{\text{inch}}$)

Typical Characteristics

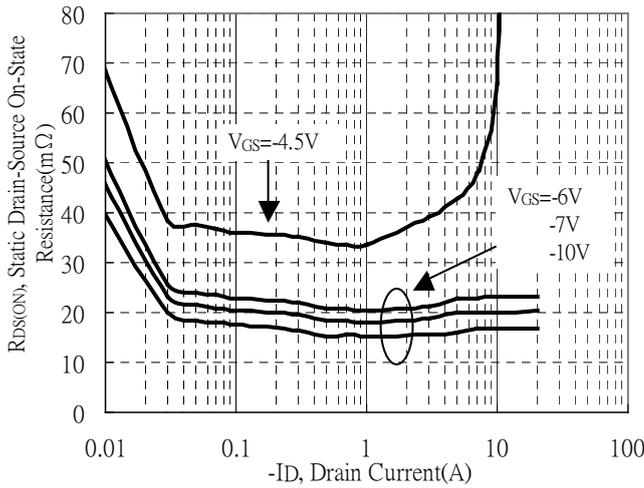
Typical Output Characteristics



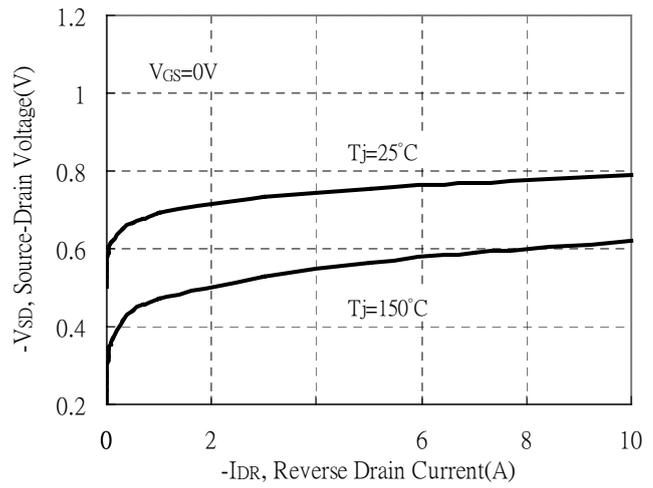
Breakdown Voltage vs Ambient Temperature



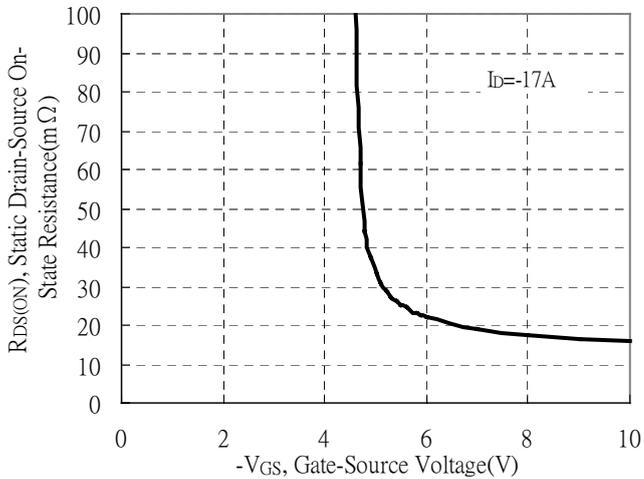
Static Drain-Source On-State resistance vs Drain Current



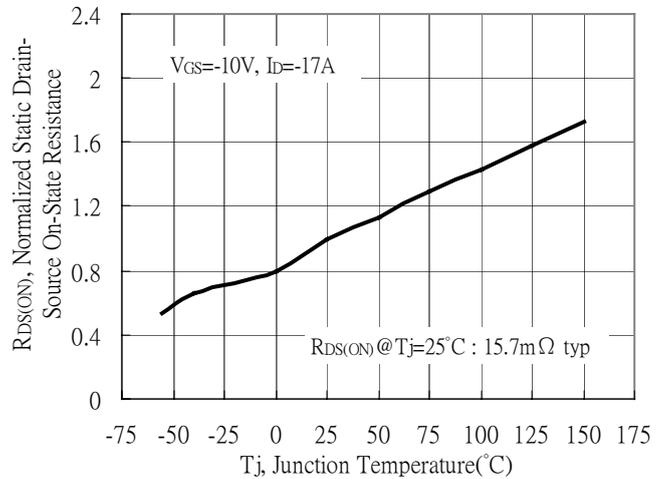
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

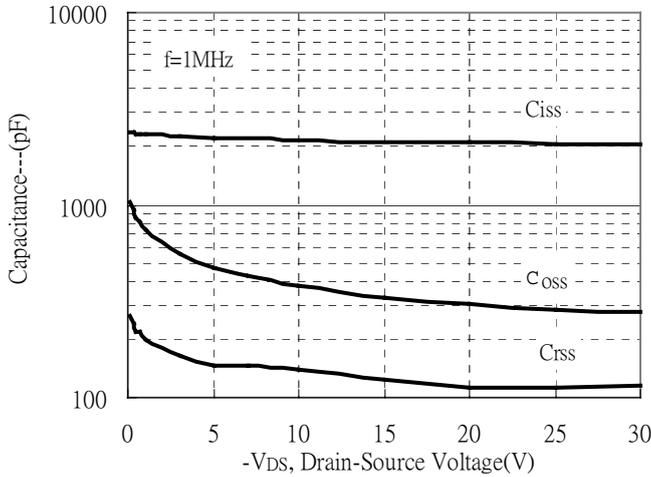


Drain-Source On-State Resistance vs Junction Temperature

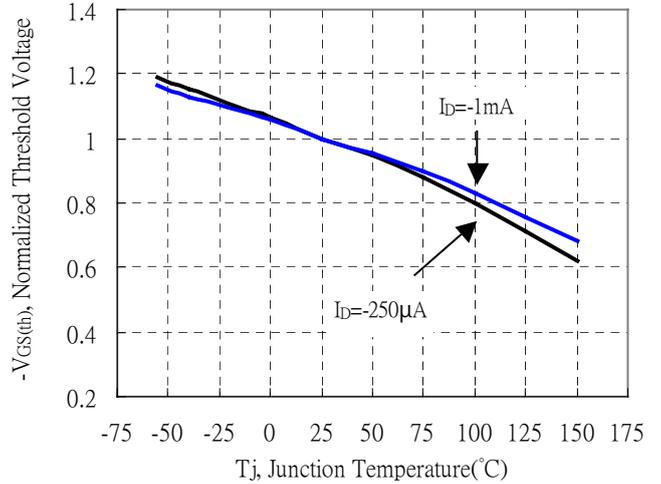


Typical Characteristics(Cont.)

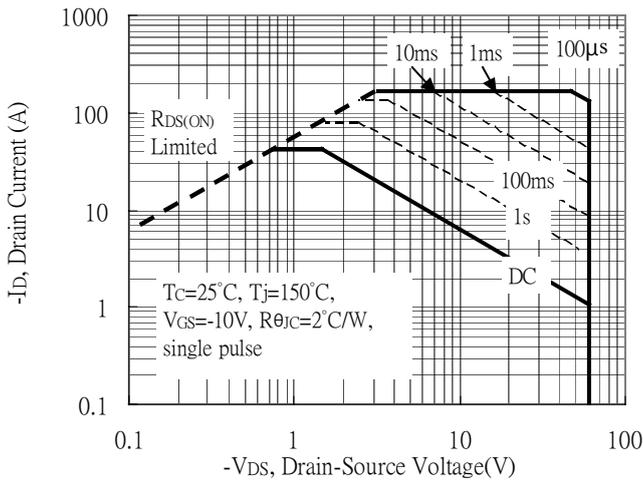
Capacitance vs Drain-to-Source Voltage



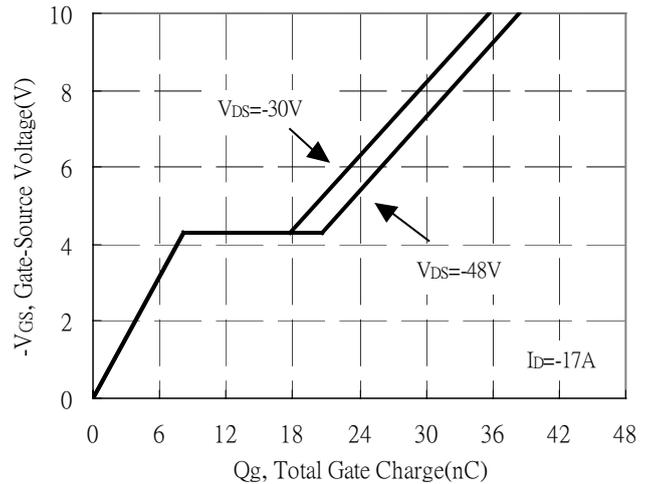
Threshold Voltage vs Junction Temperature



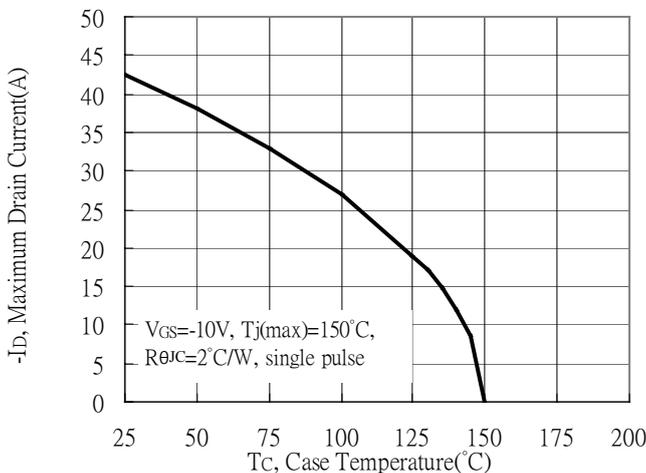
Maximum Safe Operating Area



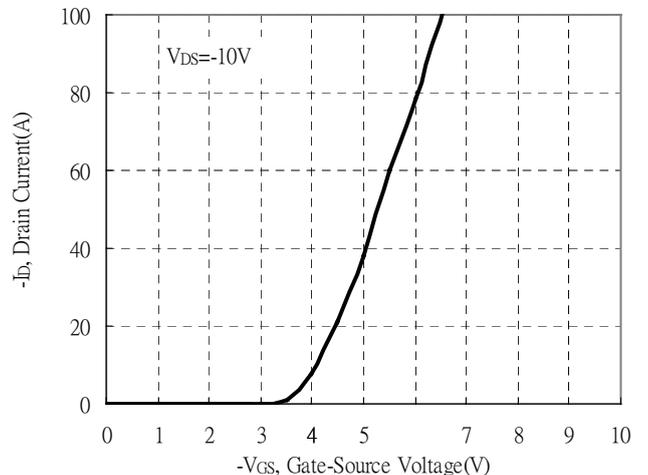
Gate Charge Characteristics



Maximum Drain Current vs Case Temperature

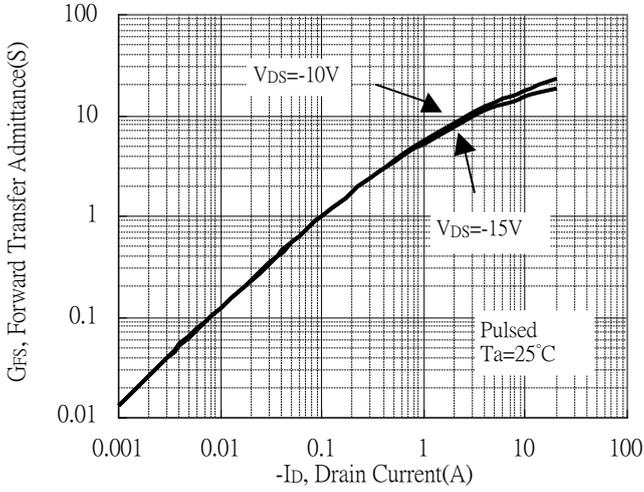


Typical Transfer Characteristics

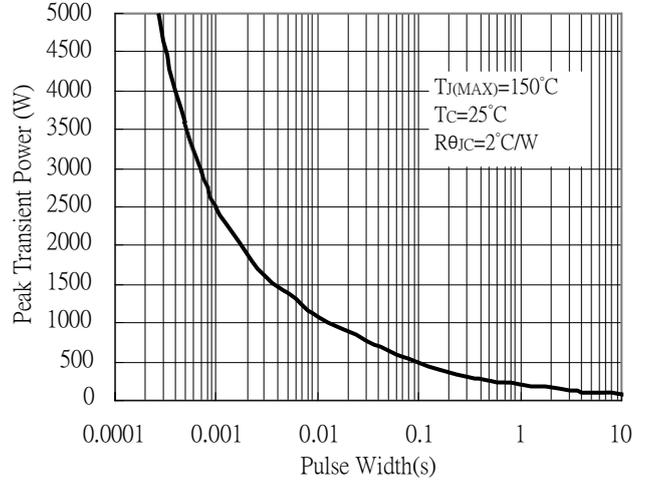


Typical Characteristics(Cont.)

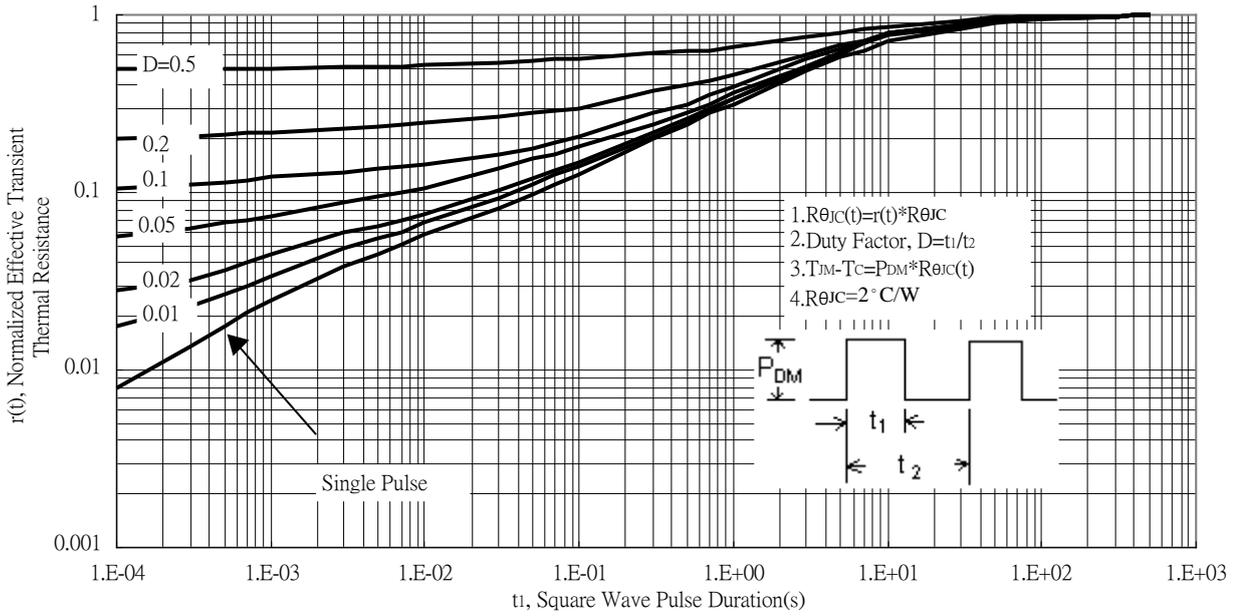
Forward Transfer Admittance vs Drain Current



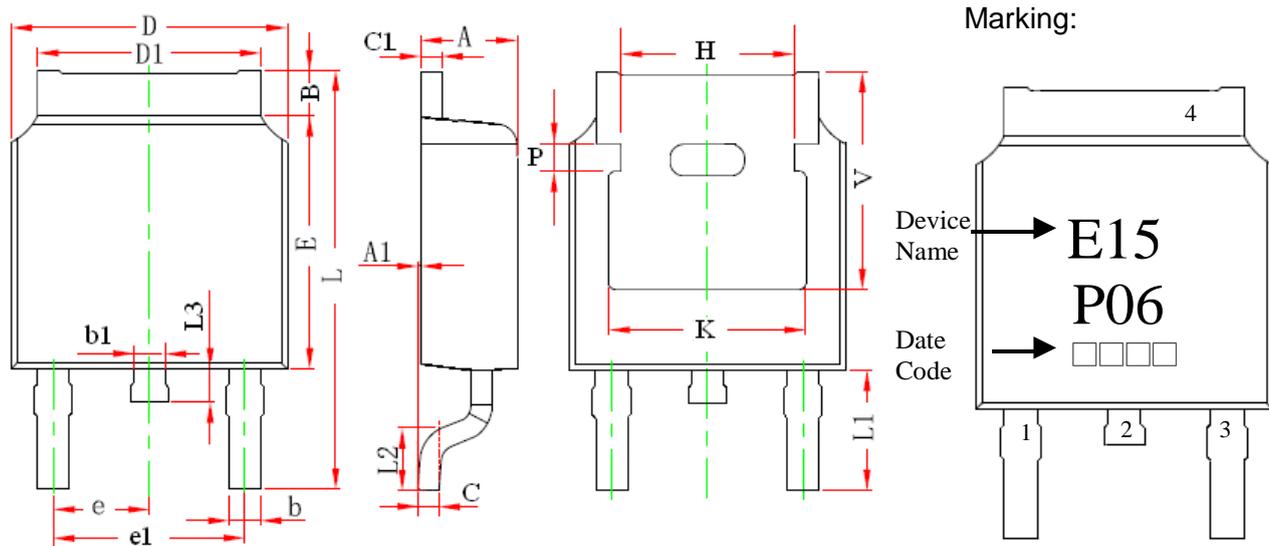
Single Pulse Maximum Power Dissipation



Transient Thermal Response Curves



TO-252 Dimension



3-Lead TO-252 Plastic Surface Mount Package

Style: Pin 1.Gate 2.Drain 3.Source 4.Drain

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	e	0.086	0.094	2.186	2.386
A1	0.000	0.005	0.000	0.127	e1	0.172	0.188	4.372	4.772
B	0.039	0.048	0.990	1.210	H	0.163	REF	4.140	REF
b	0.026	0.034	0.660	0.860	K	0.190	REF	4.830	REF
b1	0.026	0.034	0.660	0.860	L	0.386	0.409	9.800	10.400
C	0.018	0.023	0.460	0.580	L1	0.114	REF	2.900	REF
C1	0.018	0.023	0.460	0.580	L2	0.055	0.067	1.400	1.700
D	0.256	0.264	6.500	6.700	L3	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	P	0.026	REF	0.650	REF
E	0.236	0.244	6.000	6.200	V	0.211	REF	5.350	REF